

MGF2124G

**FOR MICROWAVE POWER AMPLIFIERS
 CHIP-CARRIER TYPE**

6249829 MITSUBISHI (DISCRETE SC)

91D 10098 DT-39-05

DESCRIPTION

The MGF2124G combines the advantages of the least parasitics of a chip device and the easy assembly of a package device. The device gives excellent performance even in Ku-band.

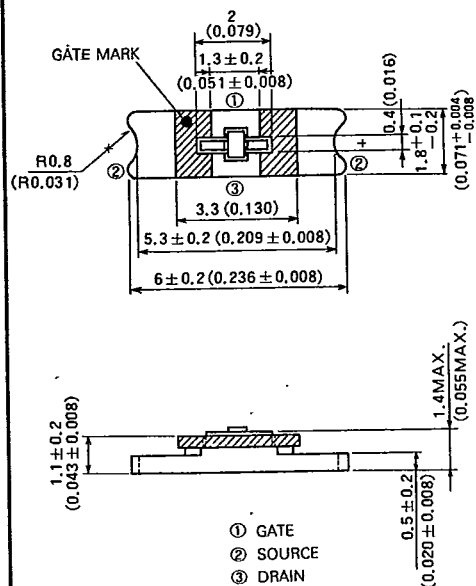
FEATURES

- Chip-carrier type 1.8 mm Width
- Flip-chip mounted.
- High output power
 $P_{1dB} = 0.7 \text{ W (TYP.) @ } f = 14 \text{ GHz}$
- High linear power gain
 $G_{LP} = 5.5 \text{ dB (TYP.) @ } f = 14 \text{ GHz}$
- High power added efficiency
 $\eta_{add} = 18\% \text{ (TYP.) @ } f = 14 \text{ GHz, } P_{1dB}$

QUALITY GRADE

- IG

OUTLINE DRAWING Unit: millimeters (inches)



ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Rating	Unit
V_{GD0}	Gate to drain voltage	-11	V
V_{GS0}	Gate to source voltage	-11	V
I_D	Drain current	800	mA
I_{GR}	Reverse gate current	-2.0	mA
I_{GF}	Forward gate current	4.5	mA
P_T	Total power dissipation	5	W
T_{ch}	Channel temperature	175	$^\circ\text{C}$
T_{stg}	Storage temperature	-55 ~ +175	$^\circ\text{C}$
$R_{th}(ch-c)$	Thermal resistance	30	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
I_{DSS}	Saturated drain current	$V_{DS}=3\text{V}, V_{GS}=0\text{V}$	450	650	800	mA
$V_{GS(off)}$	Gate to source cut-off voltage	$V_{DS}=3\text{V}, I_D=1\text{mA}$	-2		-7	V
g_m	Transconductance	$V_{DS}=3\text{V}, I_D=300\text{mA}$	180	250		mS
$P_{1dB} *$	Output power at 1 dB gain compression	$V_{DS}=8\text{V}, I_D=300\text{mA}$	$f=12\text{GHz}$	0.7	1.0	W
			$f=14\text{GHz}$		0.7	
$G_{LP} *$	Linear power gain	$V_{DS}=8\text{V}, I_D=300\text{mA}$	$f=12\text{GHz}$	5.3	6.3	dB
			$f=14\text{GHz}$		5.5	
$\eta_{add} *$	Power added efficiency	$V_{DS}=8\text{V}, I_D=300\text{mA}$	$f=12\text{GHz}$	25		%
			$f=14\text{GHz}$		18	

* Sampling inspection



MGF2124G

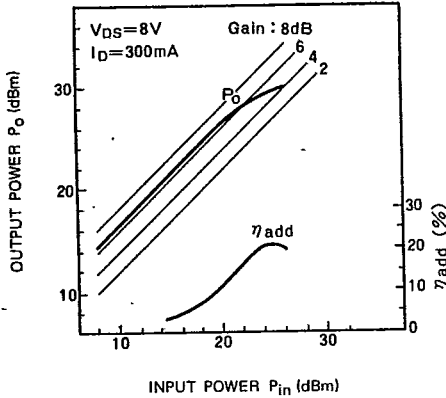
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91D 10099 D
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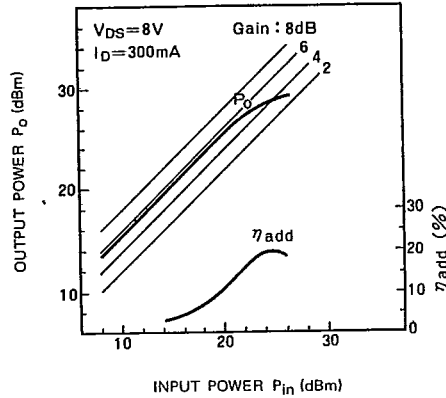
T-39-05

TYPICAL CHARACTERISTICS (Ta=25°C)

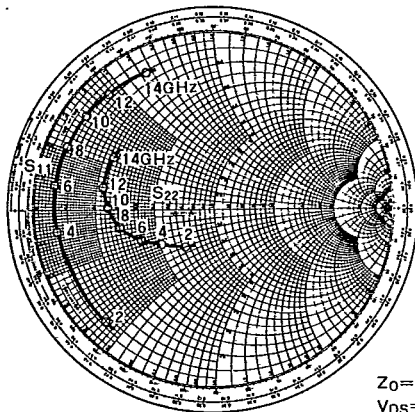
**P_o, η_{add} vs. P_{in}
 (f = 12 GHz)**



**P_o, η_{add} vs. P_{in}
 (f = 14 GHz)**

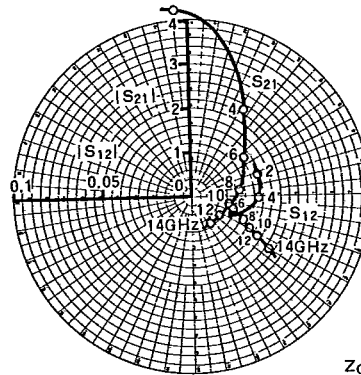


S₁₁, S₂₂ vs. f



Z₀ = 50 Ω
 V_{DS} = 8V
 I_D = 300mA

S₁₂, S₂₁ vs. f



Z₀ = 50 Ω
 V_{DS} = 8V
 I_D = 300mA

S PARAMETERS (Ta=25°C, V_{DS}=8V, I_D=300mA)

f (GHz)	S Parameters (TYP.)							
	S ₁₁		S ₁₂		S ₂₁		S ₂₂	
	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)
2	0.868	-132.1	0.033	21.9	4.26	95.1	0.245	-126.4
4	0.869	-172.1	0.034	-1.5	2.22	58.7	0.342	-146.3
6	0.863	172.0	0.016	-5.3	1.57	34.5	0.433	-157.4
8	0.889	155.0	0.033	-20.3	1.09	6.7	0.520	-169.5
10	0.891	143.1	0.038	-26.8	0.80	-10.4	0.578	179.0
12	0.890	132.0	0.047	-29.3	0.78	-30.8	0.625	167.8
14	0.863	115.7	0.051	-35.3	0.72	-55.8	0.612	152.3